

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,939,756 B1  
APPLICATION NO. : 09/818193  
DATED : September 6, 2005  
INVENTOR(S) : Gilyong Chung et al.

Page 1 of 1

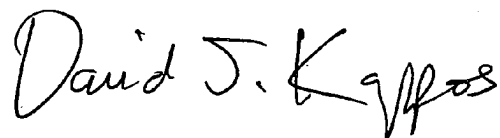
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Title:

“Inclusion Of Nitrogen At The Silicon Dioxide-Silicon Carbide Interace For Passivation Of  
Interface Defects” **should read** -- Inclusion Of Nitrogen At The Silicon Dioxide-Silicon Carbide  
Interface For Passivation Of Interface Defects --.

Signed and Sealed this

Thirteenth Day of July, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large, stylized 'D' and 'K'.

David J. Kappos  
*Director of the United States Patent and Trademark Office*